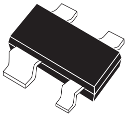
BAS56

DUAL HIGH CURRENT SWITCHING DIODE



SOT-143 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR BAS56 type is an ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in an epoxy molded surface mount package with isolated dual diodes, designed for high current, high speed switching applications.
Marking code is L51.

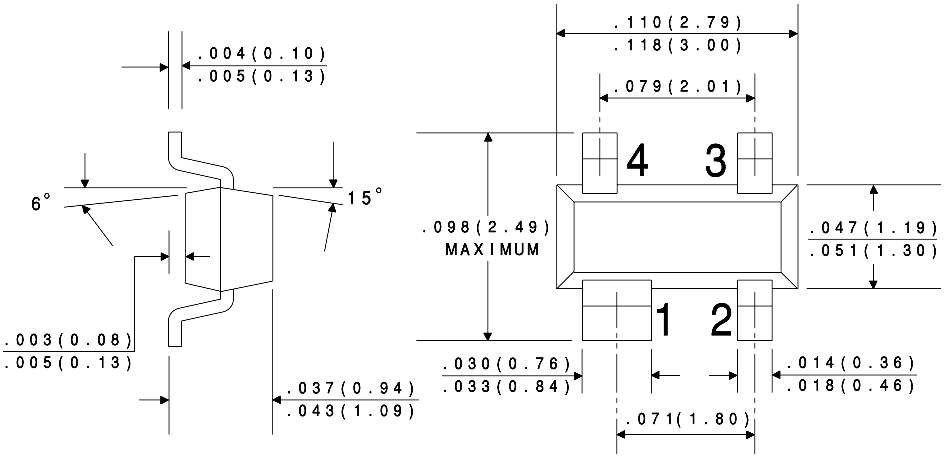
MAXIMUM RATINGS (T_A=25^{o}C)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	60	V
Peak Repetitive Reverse Voltage	V_{RRM}	60	V
Continuous Forward Current	I_F	200	mA
Peak Repetitive Forward Current	I_{FRM}	600	mA
Forward Surge Current, tp=1 µsec.	I_{FSM}	4000	mA
Forward Surge Current, tp=1 sec.	I_{FSM}	1000	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	^{o}C
Thermal Resistance	Θ_{JA}	357	^{o}C/W

ELECTRICAL CHARACTERISTICS (T_A=25^{o}C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	V_R=60V		100	nA
I_R	V_R=60V, T_A=150^{o}C		100	µA
I_R	V_R=75V		10	µA
V_F	I_F=10mA		0.75	V
V_F	I_F=200mA		1.00	V
V_F	I_F=500mA		1.25	V
C_T	V_R=0, f=1 MHz		2.5	pF
t_{rr}	I_F=I_R=400mA, R_L=100Ω, Rec. to 40mA		6.0	ns
Q_s	I_F=10mA, V_R=5.0V, R_L=500Ω		50	pC
V_{FR}	I_F=400mA, t_r=30ns		1.2	V
V_{FR}	I_F=400mA, t_r=100ns		1.5	V

All dimensions in inches (mm).



LEAD CODE:

1) ANODE 1
2) ANODE 2
3) CATHODE 2
4) CATHODE 1

R2